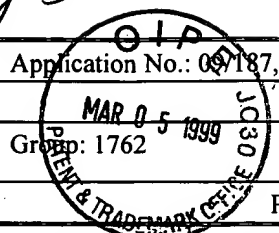


Page 1 of 3

2

FORM PTO-1449 (Modified)		Attorney Docket No.: A524R1/T289		Application No.: 09/187,551		
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Applicant: MUSAKA et al.				
		Filing Date: November 5, 1998				Group: 1762
Reference Designation		U.S. PATENT DOCUMENTS				Page 1
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
AK	✓ 5,462,899	10/31/95	Ikeda	438	238	11/30/93
AB	✓ 5,429,995	07/04/95	Nishiyama et al.	437	238	07/16/93
* AC	* 5,420,075	05/30/95	Homma et al. ✓	437	195	04/14/93
AD	5,413,967	05/09/95	Matsuda et al. ✓	437	235	05/03/94
AE	5,407,529	04/18/95	Homma ✓	156	643	03/04/93
AF	5,403,630	04/04/95	Matsui et al. ✓	427	583	10/27/93
AG	5,399,529	03/21/95	Homma ✓	437	195	05/26/93
AH	5,385,763	01/31/95	Okano et al. ✓	427	572	03/01/94
AI	✓ 5,356,722	10/18/94	Nguyen et al.	427	569	06/10/92
AJ	5,334,552	08/02/94	Homma ✓	437	195	11/24/92
AK	5,319,247	06/07/94	Matsuura ✓	257	760	10/25/91
* AL	✓ 5,288,518	02/22/94	Homma	427	255.1	06/05/92
AM	✓ 5,286,518	02/15/94	Cain, et al.	427	96	04/30/92
AN	5,279,865	01/18/94	Chebi et al. ✓	427	574	06/28/91
AO	✓ 5,275,977	01/04/94	Otsubo et al.	437	235	03/14/91
AP	✓ 5,223,457	06/29/93	Mintz, et al.	437	225	10/11/91
AQ	5,215,787	06/01/93	Homma ✓	427	248.1	01/14/92
AR	✓ 5,206,060	04/27/93	Balian, et al.	427	489	08/09/90
AS	5,156,881	10/20/92	Okano et al. ✓	427	572	04/16/91
AT	✓ 5,013,691	05/07/91	Lory et al.	437	238	07/31/89
AU	✓ 4,894,352	01/16/90	Lane et al.	437	238	10/26/88
AV	✓ 4,872,947	10/10/89	Wang et al.	156	643	10/26/88
AW	4,851,370	07/25/89	Doklan et al. ✓	437	225	12/28/87
AX	✓ 4,818,563	04/04/89	Ishihara et al.	427	55	02/20/86
AY	✓ 4,778,721	10/18/88	Sliemers et al.	427	336	07/09/86
AZ	4,668,365	05/26/87	Foster et al.	427	192.23	10/25/84
BA	✓ 4,461,783	07/24/84	Yamazaki	427	39	09/30/82

RECEIVED

MAR 09 1999

GROUP 1700

reviewed in 08/25/99, 554

Marianne L. Roberts

5/13/99

BB	✓	4,282,267	08/04/81	Küyel	427	38	03/05/80
FOREIGN PATENT DOCUMENTS							
		Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)
BC		4-239750	08/27/92	JP	H01 L21	90	No (abstract only)
BD		4-341568	11/27/92	JP	C23C 16	40	No (abstract only)
BE		J6 1276-977-A	12/06/86	JP	C23C 16	50	No (abstract only)
BF	✓	WO 92/20833	11/26/92	PCT <i>Wrise</i>	C23C	16/00	yes
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
BG		Carl et al., "The Effect of O ₂ :C ₂ F ₆ Ratios and Low Frequency Power On The Gap Fill Properties And Stability Of F-TEOS Films", DUMIC Conference, Feb. 1995, pp. 234-240.					
BH		Chang et al., "Frequency Effects and Properties of Plasma Deposited Fluorinated Silicon Nitride", J. Vac. Sci. Technol. B6 (2) 1988, pp. 524-532. <i>March/april</i>					
BI		Fukada et al., "Preparation Of SiOF Films With Low Dielectric Constant By ECR Plasma CVD", DUMIC Conference, Feb. 1995, pp. 43-49.					
BJ		Galiano et al., "Stress-Temperature Behavior of Oxide Films Used For Intermetal Dielectric Applications", VMIC Conference, June 1992, pp. 100-106.					
BK		Hayasaka et al., "High-Quality And Low Dielectric Constant SiO ₂ CVD Using High Density Plasma", Dry Process Symposium, Nov. 1994 , pp. 163-168. <i>Nov. 1-2, 1993</i>					
BL		Hoff et al., "Thermal Oxidation Of Silicon In An Afterglow Gas", (undated), Ctr. for Elect. Materials and Devices, Penn State Univ. - <i>no date, but after 1987</i>					
BM		Laxman, Ravi K. "Low ε Dielectrics: CVD Fluorinated Silicon Dioxides", Semiconductor International, May 1995, pp. 71-74.					
BN		Matsuda et al., "Dual Frequency Plasma CVD Fluorosilicate Glass Deposition For 0.25 μm Interlevel Dielectrics", DUMIC Conference, Feb. 1995, pp. 22-28.					
BO		Musaka et al., "Single Step Gap Filling Technology For Subhalf Micron Metal Spacings On Plasma Enhanced TEOS/O ₂ Chemical Vapor Deposition System", Extended Abstracts of the 1993 International Conference on Solid State Devices and Materials, Makuhari, 1993, pp. 510-512. <i>No month</i>					
BP		Qian et al., "High Density Plasma Deposition And Deep Submicron Gap Fill With Low Dielectric Constant SIOF Films", DUMIC Conference, Feb. 1995, pp. 50-56.					
BQ		Robles et al., "Effects of RF Frequency and Deposition Rates on the Moisture Resistance of PECVD TEOS-Based Oxide Films", Vol. 92-1, ECS Extended Abstracts, p. 215, Abstract 129, May 1992.					
BR		Shapiro et al., "Dual Frequency Plasma CVD Fluorosilicate Glass Water Absorption And Stability", DUMIC Conference, Feb. 1995, pp. 118-123					
BS		Takeishi et al., "Stabilizing Dielectric Constants of Fluorine-Doped-SiO ₂ Films by N ₂ O-Plasma Annealing", DUMIC Conference, Feb. 1995, pp. 257-259.					

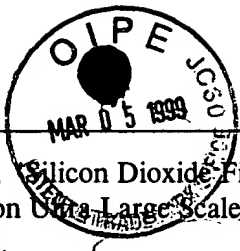
RECEIVED

MAR 09 1999

GROUP 1700

5/13/99

[Signature]



Page 3 of 3

BT	Webb et al., "Silicon Dioxide Films Produced By PECVD of TEOS and TMCTS", Proceedings of the Int. Symp. on Ultra-Large Scale Integration Science and Technology, No. 9, 1989, Pennington, N.J., pp. 571-585. <i>no month</i>
BU	Yu et al., "Step Coverage Study of Peteos Deposition For Intermetal Dielectric Applications", VMIC Conference, Jun. 1990, 166-172.
BV	Kouvatsos et al., "Fluorine Enhanced Oxidation of Silicon: Effect of Fluorine on Oxide Stress", Vol. 90-2, ECS Extended Abstracts, Abstract No. 310, pp. 447, October 1990.
BW	Kouvatsos et al., "Fluorine-Enhanced Oxidation of Silicon, Effects of Fluorine on Oxide Stress and Growth Kinetics" J. Electrochem. Soc., Vol 138, No. 6, June 1991, pp. 1752-1755/.
BX	Kouvatsos et al., "SiO ₂ Film Stress-Thickness Dependence, Non-Planar Oxidation, and Fluorine-Related Effets" J. Electrochem. Soc., Vol. 139, No. 8, August 1992, pp. 2322-2326.
BY	Schravendijk et al., "Correlation Between Dielectric Reliability and Compositional Characteristics of PECVD Oxide Films" VMIC Conference 1992 ISMIC-101/92/0372, June 1992, pp. 372-378.
BZ	Homma et al., "A Room Temperature CVD Technology for Interlayer in Deep-Submicron Multilevel Interconnection" IEEE International Electron Devices Meeting, Washington, D.C., 1991, pp10.7.1-10.7.4. <i>no month</i>
EXAMINER	<i>Marion T. P. Scott</i> DATE CONSIDERED <i>5/13/99</i>

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.